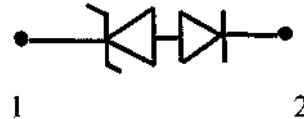
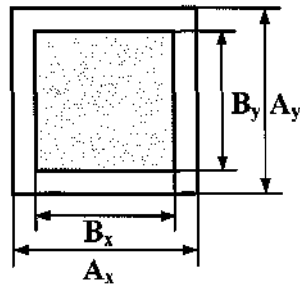


Rev.2. Jan/ 2014.

SM-2,8

Chip TVS diode.



Mechanical date: $A_x=A_y=590\mu\text{m}$
 $B_x=B_y=350\mu\text{m}$

Chip thickness: $180\pm 16\mu\text{m}$

Scribe Line width - $60\mu\text{m}$.

Top side - pin1. Al metallization for wire bond $d=2.2\pm 0.2\mu\text{m}$.

Back side - pin2. Ti-Ni-Ag for soldering.

Schematic and pinning diagram.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Peak Pulse Power	P_{pp}	$t_p=8/20\mu\text{s}$	400*	W
Peak Pulse Current	I_{pp}	$t_p=8/20\mu\text{s}$	24,0*	A
Electrostatic discharge	VESD	IEC 61000-4-2. Level-4.	+/-15,0-Contact. +/-25,0-Air.	kV
Max .junction temperature	T_j	-	+150	°C

Characteristics ($T_j=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{rwm}	Reverse Stand-off voltage		-	-	2.8	V
V_{pt}	Punch-Through Voltage.	$I_{pt}=2\mu\text{A}$	3,0	-	-	V
V_{sb}	Snap-Back Voltage.	$I_{sb}=50\text{mA}$	2,8	-	4,2	V
I_r	Reverse leakage current	$V_R=3,0\text{V}$; "+" on pin 1	-	-	0,8	μA
C_j	Diode capacitance .	$F=1\text{MHz}$, $V_{dc}=0\text{V}$.	-	50	-	pF
V_{CL}	Clamping voltage	$I_R=2\text{A}$, $t_p=8/20\mu\text{s}$ $I_R=5,0\text{A}$, $t_p=8/20\mu\text{s}$ $I_R=24,0\text{A}$, $t_D=8/20\mu\text{s}$	-	-	4,5* 5,5* 9,0*	V V

*- For Device testing.